



Description

The AOD21357 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

General Features

$V_{DS} = -30V$ $I_D = 80A$

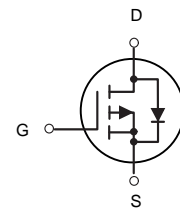
$R_{DS(ON)} < 8.8m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AOD21357	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 25	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-80	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-42	A
I_{DM}	Pulsed Drain Current ²	-172	A
EAS	Single Pulse Avalanche Energy ³	31	mJ
I_{AS}	Avalanche Current	-25	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	31.2	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	43	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	$^\circ\text{C/W}$



Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Gate-body Leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J=25^\circ\text{C}$	$V_{DS} = -24V, V_{GS} = 0V$	-	-	-1	μA
	$T_J=55^\circ\text{C}$		-	-	-5	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance ²	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -12A$	-	5.5	8.8	m Ω
		$V_{GS} = -4.5V, I_D = -8A$	-	9	14	
Forward Transconductance	g_{fs}	$V_{DS} = -5V, I_D = -20A$	-	28	-	S
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1\text{MHz}$	-	4320	-	pF
Output Capacitance	C_{oss}		-	529	-	
Reverse Transfer Capacitance	C_{rss}		-	487	-	
Gate Resistance	R_g		$V_{DS} = 0V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	4.0	
Total Gate Charge	Q_g	$V_{GS} = -10V, V_{DS} = -15V, I_D = -15A$	-	45	-	nC
Gate-Source Charge	Q_{gs}		-	8.5	-	
Gate-Drain Charge	Q_{gd}		-	12.8	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -15V, R_G = 2.5\Omega, I_D = -15A$	-	18.9	-	nS
Rise Time	t_r		-	15.7	-	
Turn-Off Delay Time	$t_{d(off)}$		-	64.8	-	
Fall Time	t_f		-	36.5	-	
Diode Forward Voltage ²	V_{SD}	$I_S = -1A, V_{GS} = 0V$	-	-	-1	V
Continuous Source Current ^{1,5}	I_S	$V_G = V_D = 0V$, Force Current	-	-	-80	A

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD} = -25V, V_{GS} = -10V, L = 0.1\text{mH}, I_{AS} = -25A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

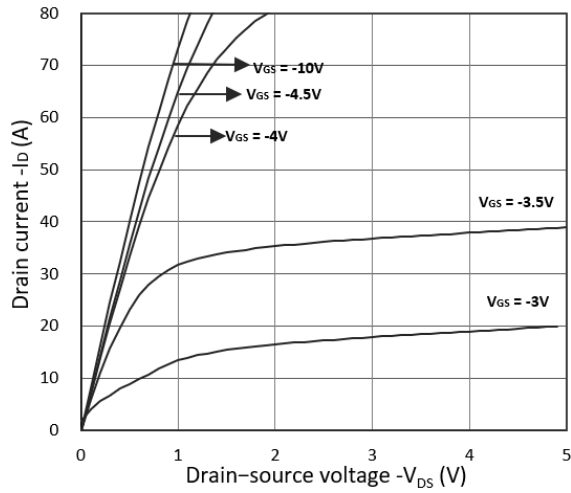


Figure 1. Output Characteristics

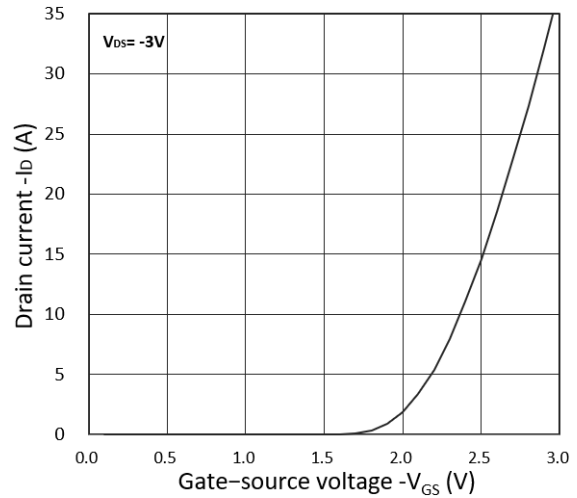


Figure 2. Transfer Characteristics

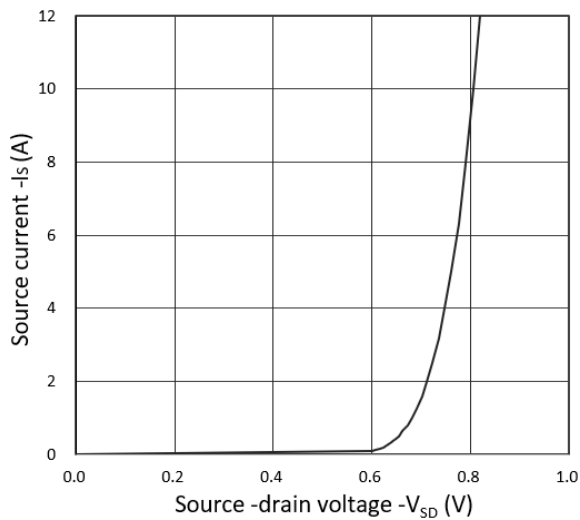


Figure 3. Forward Characteristics of Reverse

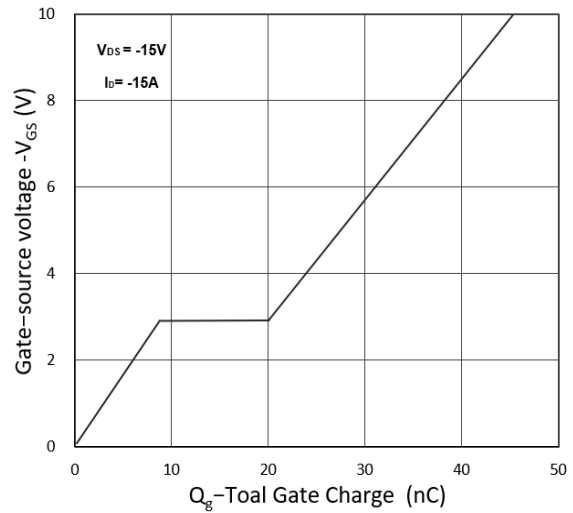


Figure 4. Gate Charge Characteristics

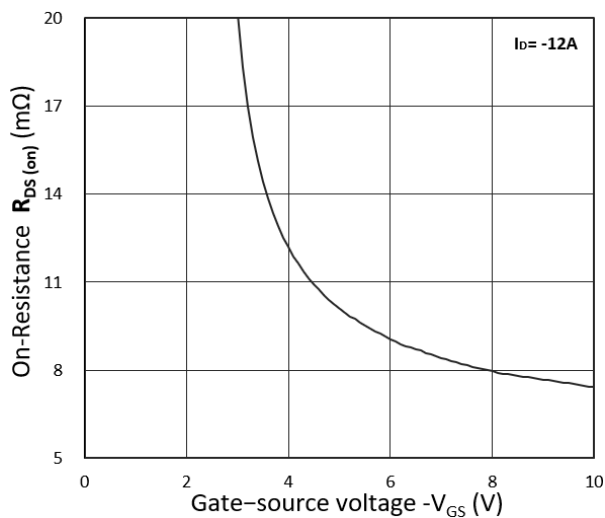


Figure 5. $R_{DS(on)}$ vs. V_{GS}

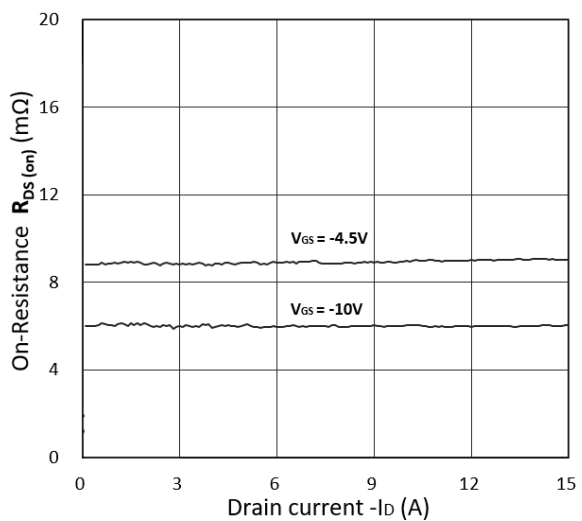


Figure 6. $R_{DS(on)}$ vs. I_D

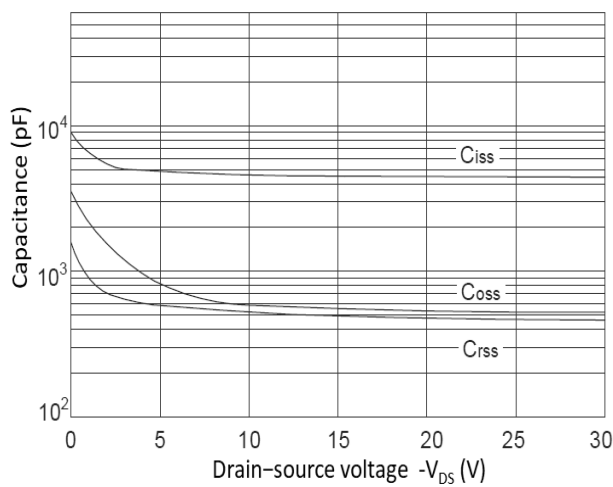


Figure 7. Capacitance Characteristics

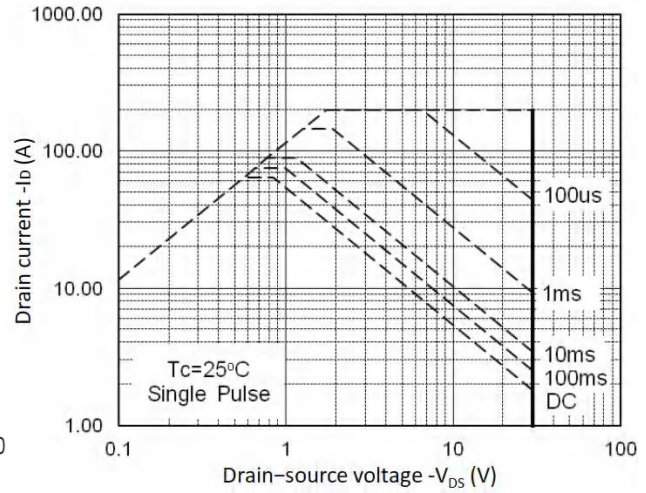


Figure 8. Safe Operating Area

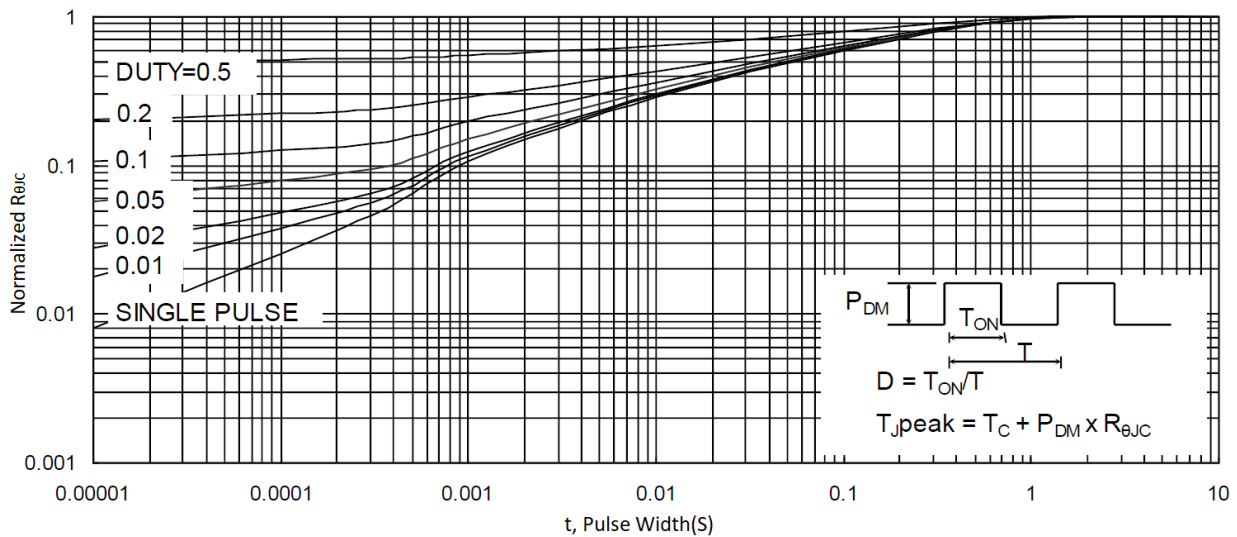


Figure 9. Normalized Maximum Transient Thermal Impedance

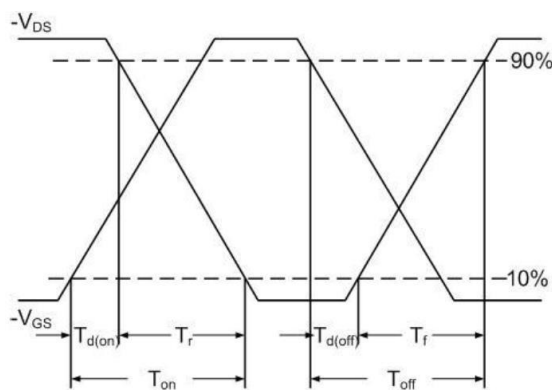


Figure 10. Switching Time Waveform

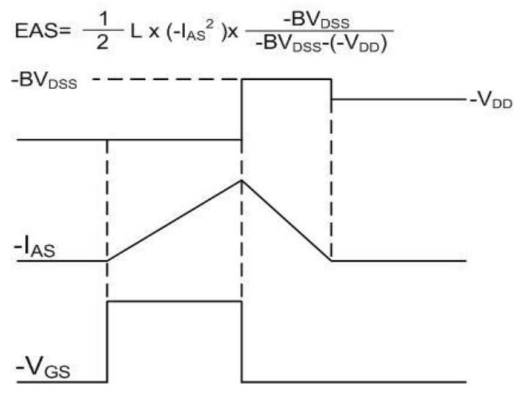
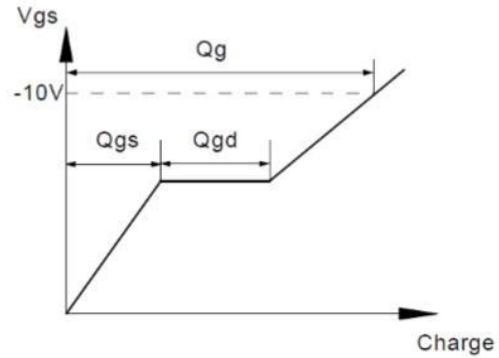
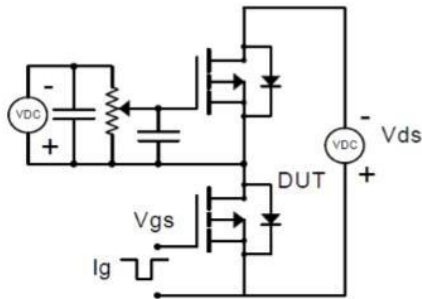


Figure 11. Unclamped Inductive Switching
Waveform

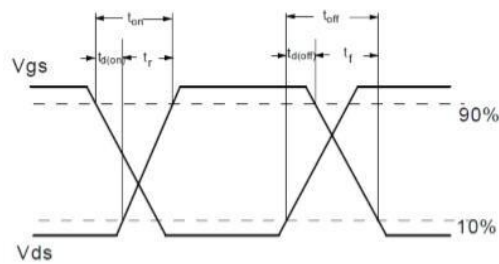
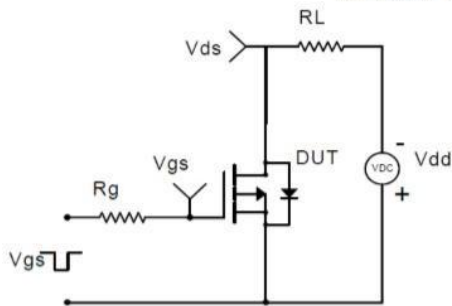


Test Circuit

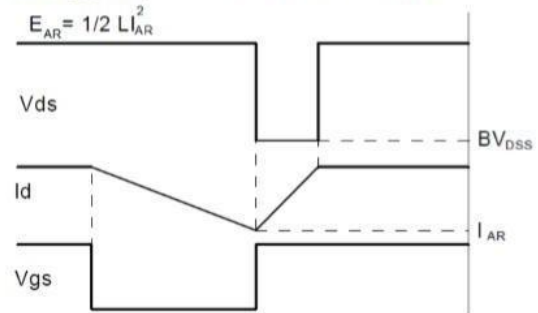
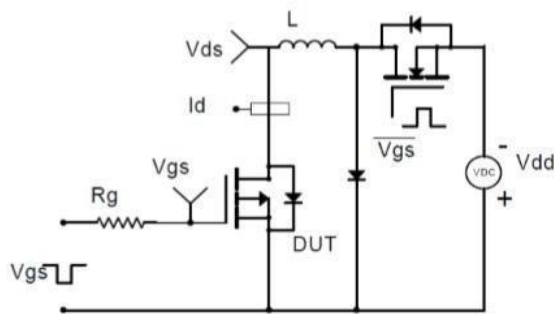
Gate Charge Test Circuit & Waveform



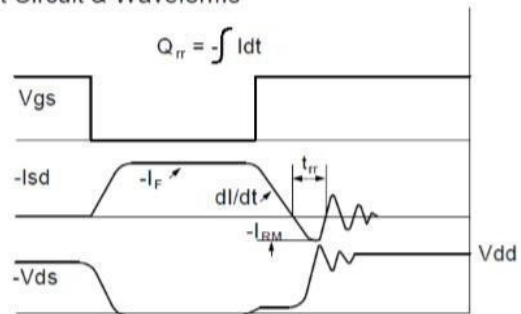
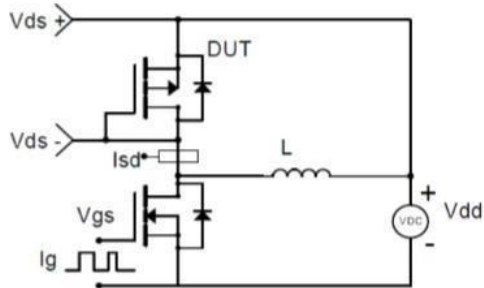
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

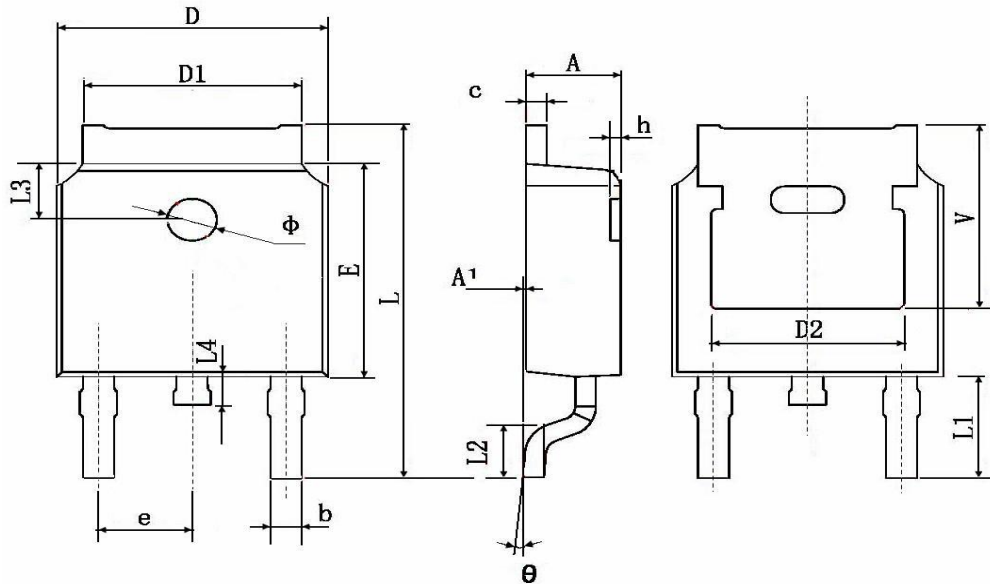


Diode Recovery Test Circuit & Waveforms





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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